

isc Silicon PNP Power Transistor

2SA900

DESCRIPTION

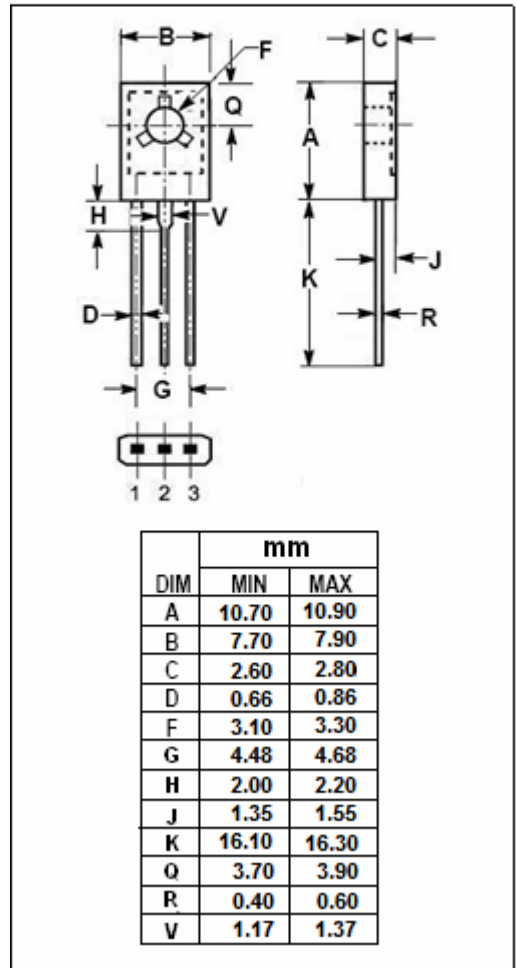
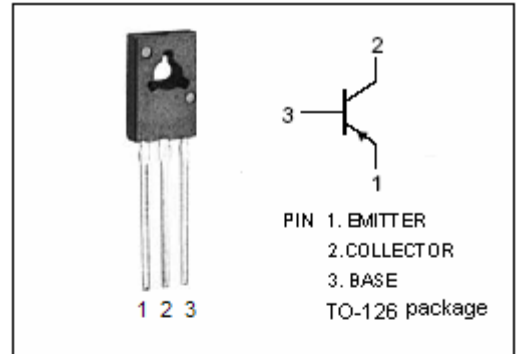
- Collector-Emitter Breakdown Voltage-
: $V_{(BR)CEO} = -18V(\text{Min})$
- Good Linearity of h_{FE}
- Low Collector Saturation Voltage
- Complement to Type 2SC1568

APPLICATIONS

- Designed for audio frequency power amplifier applications.

ABSOLUTE MAXIMUM RATINGS($T_a=25^\circ\text{C}$)

SYMBOL	PARAMETER	VALUE	UNIT
V_{CBO}	Collector-Base Voltage	-20	V
V_{CEO}	Collector-Emitter Voltage	-18	V
V_{EBO}	Emitter-Base Voltage	-5	V
I_C	Collector Current-Continuous	-1	A
I_{CP}	Collector Current-Pulse	-2	A
P_C	Collector Power Dissipation	1.2	W
T_J	Junction Temperature	150	$^\circ\text{C}$
T_{stg}	Storage Temperature Range	-55~150	$^\circ\text{C}$



isc Silicon PNP Power Transistor**2SA900****ELECTRICAL CHARACTERISTICS** $T_C=25^\circ\text{C}$ unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
$V_{(BR)CEO}$	Collector-Emitter Breakdown Voltage	$I_C = -1\text{mA}; I_B = 0$	-18			V
$V_{(BR)CBO}$	Collector-Base Breakdown Voltage	$I_C = -10\ \mu\text{A}; I_E = 0$	-20			V
$V_{(BR)EBO}$	Emitter-Base Breakdown Voltage	$I_E = -10\ \mu\text{A}; I_C = 0$	-5			V
$V_{CE(sat)}$	Collector-Emitter Saturation Voltage	$I_C = -1\text{A}; I_B = -50\text{mA}$			-0.5	V
$V_{BE(sat)}$	Base-Emitter Saturation Voltage	$I_C = -0.5\text{A}; I_B = -50\text{mA}$			-1.2	V
I_{CBO}	Collector Cutoff Current	$V_{CB} = -10\text{V}; I_E = 0$			-1	μA
I_{CEO}	Collector Cutoff Current	$V_{CE} = -18\text{V}; I_B = 0$			-10	μA
h_{FE-1}	DC Current Gain	$I_C = -0.5\text{A}; V_{CE} = -2\text{V}$	90		470	
h_{FE-2}	DC Current Gain	$I_C = -1.5\text{A}; V_{CE} = -2\text{V}$	50			
f_T	Current-Gain—Bandwidth Product	$I_C = -50\text{mA}; V_{CE} = -6\text{V}$		200		MHz
C_{OB}	Output Capacitance	$I_E = 0; V_{CB} = -6\text{V}, f_{test} = 1\text{MHz}$		40		pF

◆ **h_{FE-1} Classifications**

Q	R	S	T	U
90-155	130-210	180-280	250-360	330-470